

## 2-Bit Dual-Supply Non-Inverting Level Translator

### NLSV2T244

The NLSV2T244 is a 2-bit configurable dual-supply voltage level translator. The input  $A_n$  and output  $B_n$  ports are designed to track two different power supply rails,  $V_{CCA}$  and  $V_{CCB}$  respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input  $A_n$  to the output  $B_n$  port.

#### Features

- Wide  $V_{CCA}$  and  $V_{CCB}$  Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential  $V_{CCA}$  and  $V_{CCB}$  Sequencing
- Outputs at 3-State until Active  $V_{CC}$  is Reached
- Power-Off Protection
- Outputs Switch to 3-State with  $V_{CCB}$  at GND
- Small Packaging: UDFN8, SO-8, Micro8
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable\*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### Typical Applications

- Mobile Phones, PDAs, Other Portable Devices

#### Important Information

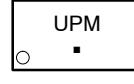
- ESD Protection for All Pins:  
HBM (Human Body Model) > 5000 V

#### MARKING DIAGRAMS



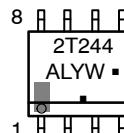
UDFN8  
MU SUFFIX  
CASE 517AJ

UP = Specific Device Code  
M = Date Code  
■ = Pb-Free Package



SO-8  
D SUFFIX  
CASE 751

A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
■ = Pb-Free Package

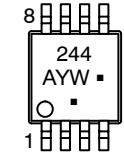


2T244  
ALYW ■



Micro8  
DM SUFFIX  
CASE 846A

A = Assembly Location  
Y = Year  
W = Work Week  
■ = Pb-Free Package



244  
AYW ■

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NLSV2T244MUTAG	UDFN8 (Pb-Free)	3000 / Tape & Reel
NLSV2T244DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel
NLSV2T244DMR2G	Micro8 (Pb-Free)	4000 / Tape & Reel
NLVS2T244DMR2G*	Micro8 (Pb-Free)	4000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NLSV2T244

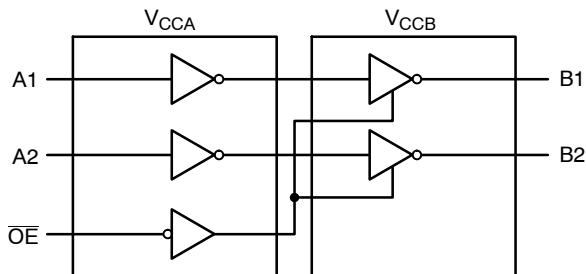
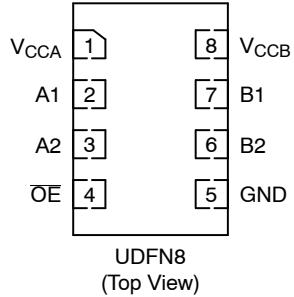
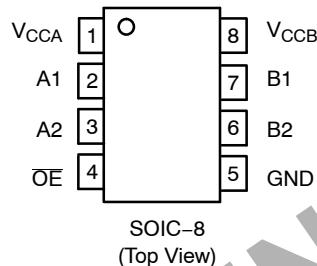


Figure 1. Logic Diagram

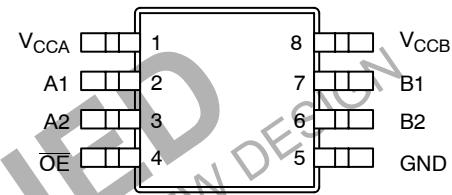
## PIN ASSIGNMENTS



UDFN8  
(Top View)



SOIC-8  
(Top View)



Micro8  
(Top View)

## PIN ASSIGNMENT

PIN	FUNCTION
V <sub>CCA</sub>	Input Port DC Power Supply
V <sub>CCB</sub>	Output Port DC Power Supply
GND	Ground
A <sub>n</sub>	Input Port
B <sub>n</sub>	Output Port
OE	Output Enable

## TRUTH TABLE

Inputs		Outputs
OE	A <sub>n</sub>	B <sub>n</sub>
L	L	L
L	H	H
H	X	3-State

## MAXIMUM RATINGS

Symbol	Rating	Value	Condition	Unit
$V_{CCA}, V_{CCB}$	DC Supply Voltage	-0.5 to +5.5		V
$V_I$	DC Input Voltage	$A_n$	-0.5 to +5.5	V
$V_C$	Control Input	$\bar{OE}$	-0.5 to +5.5	V
$V_O$	DC Output Voltage (Power Down)	$B_n$	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$
	(Active Mode)	$B_n$	-0.5 to +5.5	V
	(Tri-State Mode)	$B_n$	-0.5 to +5.5	V
$I_{IK}$	DC Input Diode Current	-20	$V_I < GND$	mA
$I_{OK}$	DC Output Diode Current	-50	$V_O < GND$	mA
$I_O$	DC Output Source/Sink Current	$\pm 50$		mA
$I_{CCA}, I_{CCB}$	DC Supply Current Per Supply Pin	$\pm 100$		mA
$I_{GND}$	DC Ground Current per Ground Pin	$\pm 100$		mA
$T_{STG}$	Storage Temperature	-65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CCA}, V_{CCB}$	Positive DC Supply Voltage	0.9	4.5	V
$V_I$	Bus Input Voltage	GND	4.5	V
$V_C$	Control Input	$\bar{OE}$	4.5	V
$V_O$	Bus Output Voltage (Power Down Mode)	GND	4.5	V
	(Active Mode)	$B_n$	GND	$V_{CCB}$
	(Tri-State Mode)	$B_n$	GND	V
$T_A$	Operating Temperature Range	-40	+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Rate $V_I$ , from 30% to 70% of $V_{CC}$ ; $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0	10	nS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	-40°C to +85°C		Unit
					Min	Max	
V <sub>IH</sub>	Input HIGH Voltage (An, OE)		3.6 – 4.5	0.9 – 4.5	2.2	–	V
			2.7 – 3.6		2.0	–	
			2.3 – 2.7		1.6	–	
			1.4 – 2.3		0.65 * V <sub>CCA</sub>	–	
			0.9 – 1.4		0.9 * V <sub>CCA</sub>	–	
V <sub>IL</sub>	Input LOW Voltage (An, OE)		3.6 – 4.5	0.9 – 4.5	–	0.8	V
			2.7 – 3.6		–	0.8	
			2.3 – 2.7		–	0.7	
			1.4 – 2.3		–	0.35 * V <sub>CCA</sub>	
			0.9 – 1.4		–	0.1 * V <sub>CCA</sub>	
V <sub>OH</sub>	Output HIGH Voltage	I <sub>OH</sub> = -100 µA; V <sub>I</sub> = V <sub>IH</sub>	0.9 – 4.5	0.9 – 4.5	V <sub>CCB</sub> – 0.2	–	V
		I <sub>OH</sub> = -0.5 mA; V <sub>I</sub> = V <sub>IH</sub>	0.9	0.9	0.75 * V <sub>CCB</sub>	–	
		I <sub>OH</sub> = -2 mA; V <sub>I</sub> = V <sub>IH</sub>	1.4	1.4	1.05	–	
		I <sub>OH</sub> = -6 mA; V <sub>I</sub> = V <sub>IH</sub>	1.65	1.65	1.25	–	
			2.3	2.3	2.0	–	
		I <sub>OH</sub> = -12 mA; V <sub>I</sub> = V <sub>IH</sub>	2.3	2.3	1.8	–	
			2.7	2.7	2.2	–	
		I <sub>OH</sub> = -18 mA; V <sub>I</sub> = V <sub>IH</sub>	2.3	2.3	1.7	–	
			3.0	3.0	2.4	–	
		I <sub>OH</sub> = -24 mA; V <sub>I</sub> = V <sub>IH</sub>	3.0	3.0	2.2	–	
V <sub>OL</sub>	Output LOW Voltage	I <sub>OL</sub> = 100 µA; V <sub>I</sub> = V <sub>IL</sub>	0.9 – 4.5	0.9 – 4.5	–	0.2	V
		I <sub>OL</sub> = 0.5 mA; V <sub>I</sub> = V <sub>IL</sub>	1.1	1.1	–	0.3	
		I <sub>OL</sub> = 2 mA; V <sub>I</sub> = V <sub>IL</sub>	1.4	1.4	–	0.35	
		I <sub>OL</sub> = 6 mA; V <sub>I</sub> = V <sub>IL</sub>	1.65	1.65	–	0.3	
		I <sub>OL</sub> = 12 mA; V <sub>I</sub> = V <sub>IL</sub>	2.3	2.3	–	0.4	
			2.7	2.7	–	0.4	
		I <sub>OL</sub> = 18 mA; V <sub>I</sub> = V <sub>IL</sub>	2.3	2.3	–	0.6	
			3.0	3.0	–	0.4	
I <sub>I</sub>	Input Leakage Current	V <sub>I</sub> = V <sub>CCA</sub> or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	µA
		OE = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	
I <sub>OFF</sub>	Power-Off Leakage Current						µA
I <sub>CCA</sub>	Quiescent Supply Current	V <sub>I</sub> = V <sub>CCA</sub> or GND; I <sub>O</sub> = 0, V <sub>CCA</sub> = V <sub>CCB</sub>	0.9 – 4.5	0.9 – 4.5	–	1.0	µA
I <sub>CCB</sub>	Quiescent Supply Current	V <sub>I</sub> = V <sub>CCA</sub> or GND; I <sub>O</sub> = 0, V <sub>CCA</sub> = V <sub>CCB</sub>	0.9 – 4.5	0.9 – 4.5	–	1.0	µA
I <sub>CCA</sub> + I <sub>CCB</sub>	Quiescent Supply Current	V <sub>I</sub> = V <sub>CCA</sub> or GND; I <sub>O</sub> = 0, V <sub>CCA</sub> = V <sub>CCB</sub>	0.9 – 4.5	0.9 – 4.5	–	2.0	µA
ΔI <sub>CCA</sub>	Increase in I <sub>CC</sub> per Input Voltage, Other Inputs at V <sub>CCA</sub> or GND	V <sub>I</sub> = V <sub>CCA</sub> – 0.6 V; V <sub>I</sub> = V <sub>CCA</sub> or GND	4.5 3.6	4.5 3.6	–	10 5.0	µA
ΔI <sub>CCB</sub>	Increase in I <sub>CC</sub> per Input Voltage, Other Inputs at V <sub>CCA</sub> or GND	V <sub>I</sub> = V <sub>CCA</sub> – 0.6 V; V <sub>I</sub> = V <sub>CCA</sub> or GND	4.5 3.6	4.5 3.6	–	10 5.0	µA
I <sub>OZ</sub>	I/O Tri-State Output Leakage Current	T <sub>A</sub> = 25°C, OE = 0 V	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TOTAL STATIC POWER CONSUMPTION ( $I_{CCA} + I_{CCB}$ )

$V_{CCA}$ (V)	-40°C to +85°C										Unit	
	$V_{CCB}$ (V)											
	4.5		3.3		2.8		1.8		0.9			
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
4.5		2		2		2		2		< 1.5	µA	
3.3		2		2		2		2		< 1.5	µA	
2.8		< 2		< 1		< 1		< 0.5		< 0.5	µA	
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	µA	
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	µA	

NOTE: Connect ground before applying supply voltage  $V_{CCA}$  or  $V_{CCB}$ . This device is designed with the feature that the power-up sequence of  $V_{CCA}$  and  $V_{CCB}$  will not damage the IC.

## AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	$V_{CCA}$ (V)	-40°C to +85°C										Unit	
			$V_{CCB}$ (V)											
			4.5		3.3		2.8		1.8		1.2			
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
$t_{PLH}$ , $t_{PHL}$ (Note 1)	Propagation Delay, $A_n$ to $B_n$	4.5		1.6		1.8		2.0		2.1		2.3	nS	
		3.3		1.7		1.9		2.1		2.3		2.6		
		2.8		1.9		2.1		2.3		2.5		2.8		
		1.8		2.1		2.4		2.5		2.7		3.0		
		1.2		2.4		2.7		2.8		3.0		3.3		
$t_{PZH}$ , $t_{PZL}$ (Note 1)	Output Enable, $\overline{OE}$ to $B_n$	4.5		2.6		3.8		4.0		4.1		4.3	nS	
		3.3		3.7		3.9		4.1		4.3		4.6		
		2.5		3.9		4.1		4.3		4.5		4.8		
		1.8		4.1		4.4		4.5		4.7		5.0		
		1.2		4.4		4.7		4.8		5.0		5.3		
$t_{PHZ}$ , $t_{PLZ}$ (Note 1)	Output Disable, $\overline{OE}$ to $B_n$	4.5		2.6		3.8		4.0		4.1		4.3	nS	
		3.3		3.7		3.9		4.1		4.3		4.6		
		2.5		3.9		4.1		4.3		4.5		4.8		
		1.8		4.1		4.4		4.5		4.7		5.0		
		1.2		4.4		4.7		4.8		5.0		5.3		
$t_{OSHL}$ , $t_{OSLH}$ (Note 1)	Output to Output Skew, Time	4.5		0.15		0.15		0.15		0.15		0.15	nS	
		3.3		0.15		0.15		0.15		0.15		0.15		
		2.5		0.15		0.15		0.15		0.15		0.15		
		1.8		0.15		0.15		0.15		0.15		0.15		
		1.2		0.15		0.15		0.15		0.15		0.15		

1. Propagation delays defined per Figure 2.

## CAPACITANCE

Symbol	Parameter	Test Conditions						Typ (Note 2)	Unit
$C_{IN}$	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3$ V, $V_I = 0$ V or $V_{CCA/B}$						3.5	pF
$C_{I/O}$	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3$ V, $V_I = 0$ V or $V_{CCA/B}$						5.0	pF
$C_{PD}$	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3$ V, $V_I = 0$ V or $V_{CCA}$ , $f = 10$ MHz						20	pF

2. Typical values are at  $T_A = +25^\circ\text{C}$ .

3.  $C_{PD}$  is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from:  
 $I_{CC(\text{operating})} \cong C_{PD} \times V_{CC} \times f_{IN} \times N_{SW}$  where  $I_{CC} = I_{CCA} + I_{CCB}$  and  $N_{SW}$  = total number of outputs switching.

# NLSV2T244

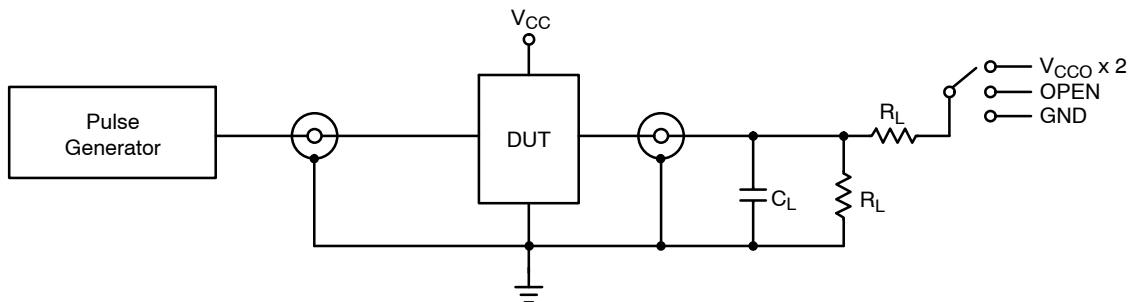
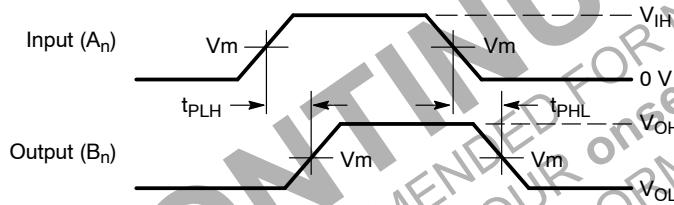


Figure 2. AC (Propagation Delay) Test Circuit

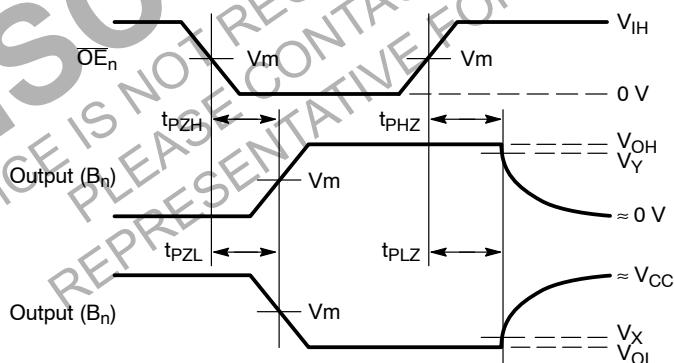
Test	Switch
$t_{PLH}, t_{PHL}$	OPEN
$t_{PLZ}, t_{PZL}$	$V_{CCO} \times 2$
$t_{PHZ}, t_{PZH}$	GND

$C_L = 15 \text{ pF}$  or equivalent (includes probe and jig capacitance)  
 $R_L = 2 \text{ k}\Omega$  or equivalent  
 $Z_{OUT}$  of pulse generator =  $50 \Omega$



Waveform 1 – Propagation Delays

$t_R = t_F = 2.0 \text{ ns}$ , 10% to 90%;  $f = 1 \text{ MHz}$ ;  $t_W = 500 \text{ ns}$



Waveform 2 – Output Enable and Disable Times

$t_R = t_F = 2.0 \text{ ns}$ , 10% to 90%;  $f = 1 \text{ MHz}$ ;  $t_W = 500 \text{ ns}$

Figure 3. AC (Propagation Delay) Test Circuit Waveforms

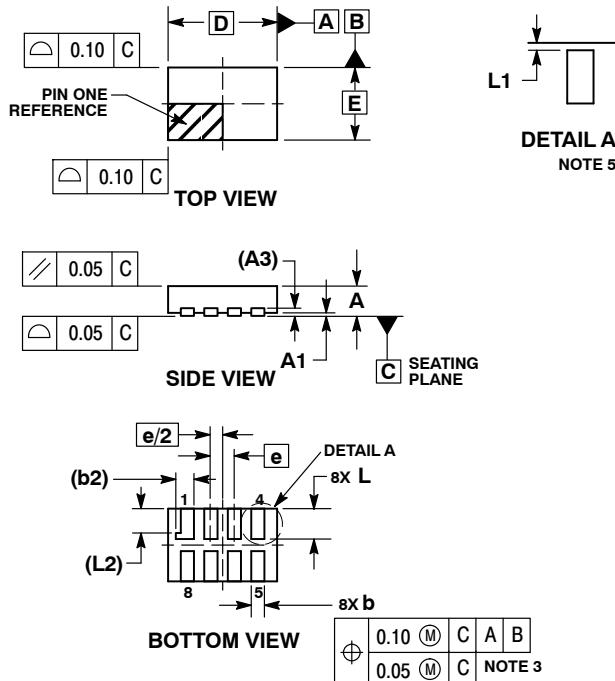
Symbol	$V_{CC}$				
	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V
$V_{mA}$	$V_{CCA}/2$	$V_{CCA}/2$	$V_{CCA}/2$	$V_{CCA}/2$	$V_{CCA}/2$
$V_{mB}$	$V_{CCB}/2$	$V_{CCB}/2$	$V_{CCB}/2$	$V_{CCB}/2$	$V_{CCB}/2$
$V_X$	$V_{OL} \times 0.1$				
$V_Y$	$V_{OH} \times 0.9$				



SCALE 4:1

**UDFN8 1.8x1.2, 0.4P**  
CASE 517AJ  
ISSUE O

DATE 08 NOV 2006



## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
4. MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 onto BOTTOM SURFACE OF TERMINALS.
5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
b2	0.30 REF	
D	1.80 BSC	
E	1.20 BSC	
L	0.45	0.55
L1	0.00	0.03
L2	0.40 REF	

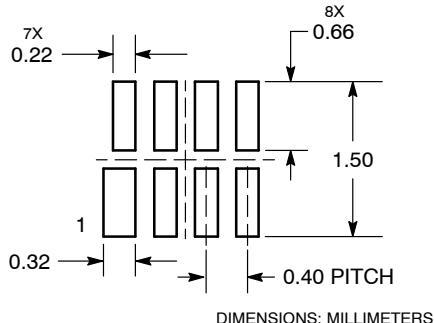
GENERIC  
MARKING DIAGRAM\*

XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "■", may or may not be present.

MOUNTING FOOTPRINT  
SOLDERMASK DEFINED

DIMENSIONS: MILLIMETERS

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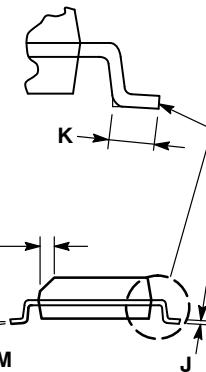
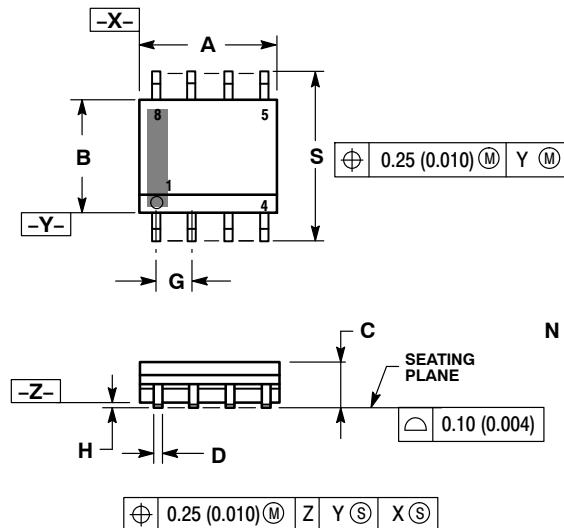
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SCALE 1:1

SOIC-8 NB  
CASE 751-07  
ISSUE AK

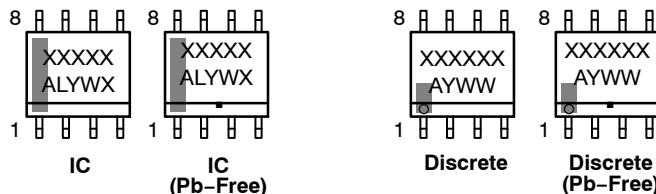
DATE 16 FEB 2011



## NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC  
MARKING DIAGRAM\*

XXXXX = Specific Device Code  
 A = Assembly Location  
 L = Wafer Lot  
 Y = Year  
 W = Work Week  
 ▪ = Pb-Free Package

XXXXXX = Specific Device Code  
 A = Assembly Location  
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\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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**SOIC-8 NB**  
**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

STYLE 1: PIN 1. Emitter 2. Collector 3. Collector 4. Emitter 5. Emitter 6. Base 7. Base 8. Emitter	STYLE 2: PIN 1. Collector, Die #1 2. Collector, #1 3. Collector, #2 4. Collector, #2 5. Base, #2 6. Emitter, #2 7. Base, #1 8. Emitter, #1	STYLE 3: PIN 1. Drain, Die #1 2. Drain, #1 3. Drain, #2 4. Drain, #2 5. Gate, #2 6. Source, #2 7. Gate, #1 8. Source, #1	STYLE 4: PIN 1. Anode 2. Anode 3. Anode 4. Anode 5. Anode 6. Anode 7. Anode 8. Common Cathode
STYLE 5: PIN 1. Drain 2. Drain 3. Drain 4. Drain 5. Gate 6. Gate 7. Source 8. Source	STYLE 6: PIN 1. Source 2. Drain 3. Drain 4. Source 5. Source 6. Gate 7. Gate 8. Source	STYLE 7: PIN 1. Input 2. External Bypass 3. Third Stage Source 4. Ground 5. Drain 6. Gate 3 7. Second Stage Vd 8. First Stage Vd	STYLE 8: PIN 1. Collector, Die #1 2. Base, #1 3. Base, #2 4. Collector, #2 5. Collector, #2 6. Emitter, #2 7. Emitter, #1 8. Collector, #1
STYLE 9: PIN 1. Emitter, Common 2. Collector, Die #1 3. Collector, Die #2 4. Emitter, Common 5. Emitter, Common 6. Base, Die #2 7. Base, Die #1 8. Emitter, Common	STYLE 10: PIN 1. Ground 2. Bias 1 3. Output 4. Ground 5. Ground 6. Bias 2 7. Input 8. Ground	STYLE 11: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Drain 2 7. Drain 1 8. Drain 1	STYLE 12: PIN 1. Source 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 13: PIN 1. N.C. 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain	STYLE 14: PIN 1. N-Source 2. N-Gate 3. P-Source 4. P-Gate 5. P-Drain 6. P-Drain 7. N-Drain 8. N-Drain	STYLE 15: PIN 1. Anode 1 2. Anode 1 3. Anode 1 4. Anode 1 5. Cathode, Common 6. Cathode, Common 7. Cathode, Common 8. Cathode, Common	STYLE 16: PIN 1. Emitter, Die #1 2. Base, Die #1 3. Emitter, Die #2 4. Base, Die #2 5. Collector, Die #2 6. Collector, Die #2 7. Collector, Die #1 8. Collector, Die #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. Anode 2. Anode 3. Source 4. Gate 5. Drain 6. Drain 7. Cathode 8. Cathode	STYLE 19: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Mirror 2 7. Drain 1 8. Mirror 1	STYLE 20: PIN 1. Source (N) 2. Gate (N) 3. Source (P) 4. Gate (P) 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 21: PIN 1. Cathode 1 2. Cathode 2 3. Cathode 3 4. Cathode 4 5. Cathode 5 6. Common Anode 7. Common Anode 8. Cathode 6	STYLE 22: PIN 1. I/O Line 1 2. Common Cathode/VCC 3. Common Cathode/VCC 4. I/O Line 3 5. Common Anode/GND 6. I/O Line 4 7. I/O Line 5 8. Common Anode/GND	STYLE 23: PIN 1. Line 1 IN 2. Common Anode/GND 3. Common Anode/GND 4. Line 2 IN 5. Line 2 OUT 6. Common Anode/GND 7. Common Anode/GND 8. Line 1 OUT	STYLE 24: PIN 1. Base 2. Emitter 3. Collector/Anode 4. Collector/Anode 5. Cathode 6. Cathode 7. Collector/Anode 8. Collector/Anode
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. Enable 4. ILIMIT 5. Source 6. Source 7. Source 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBUCK 7. VBUCK 8. VIN
STYLE 29: PIN 1. Base, Die #1 2. Emitter, #1 3. Base, #2 4. Emitter, #2 5. Collector, #2 6. Collector, #2 7. Collector, #1 8. Collector, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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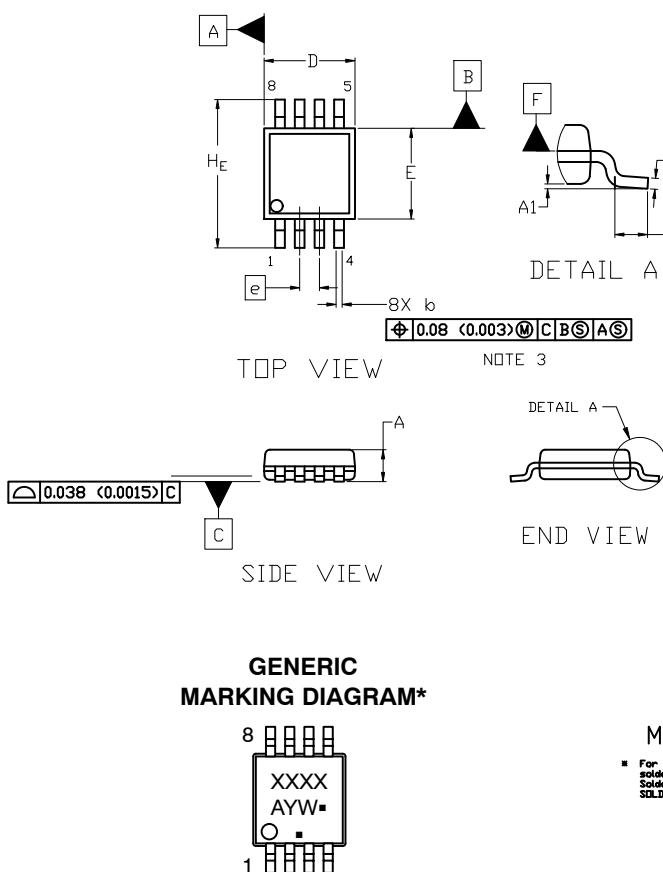
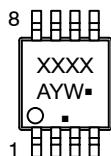
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SCALE 2:1

**Micro8**  
CASE 846A-02  
ISSUE K

DATE 16 JUL 2020


**GENERIC MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H <sub>E</sub>	4.75	4.90	5.05
L	0.40	0.55	0.70

For additional information on our Pb-Free strategy and  
existing details, please download the On Semiconductor  
Soldering and Mounting Techniques Reference Manual,  
SODERRM/D.

## STYLE 1:

PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN  
6. DRAIN  
7. DRAIN  
8. DRAIN

## STYLE 2:

PIN 1. SOURCE 1  
2. GATE 1  
3. SOURCE 2  
4. GATE 2  
5. DRAIN 1  
6. DRAIN 2  
7. DRAIN 1  
8. DRAIN 1

## STYLE 3:

PIN 1. N-SOURCE  
2. N-GATE  
3. P-SOURCE  
4. P-GATE  
5. P-DRAIN  
6. P-DRAIN  
7. N-DRAIN  
8. N-DRAIN

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